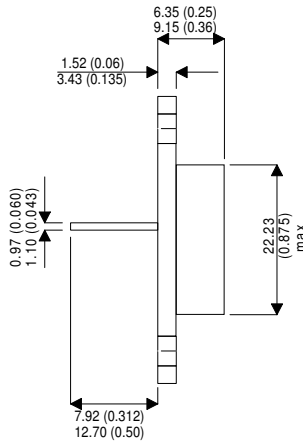
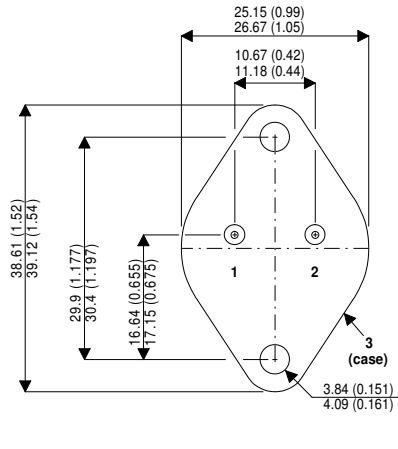


MECHANICAL DATA

Dimensions in mm (inches)



HIGH CURRENT NPN SILICON TRANSISTOR

FEATURES

- HIGH CURRENT FAST SWITCHING
- HIGH RELIABILITY
- SCREENING OPTIONS AVAILABLE

APPLICATIONS

- SWITCHING CIRCUITS
- LARGE SIGNAL/POWER AMPLIFIERS

TO3 (TO204AA)

Pin 1 = Base Pin 2 = Emitter Case = Collector

ABSOLUTE MAXIMUM RATINGS

$T_{CASE} = 25^{\circ}\text{C}$ unless otherwise stated

V_{CBO}	Collector - Base Voltage	200V
V_{CEO}	Collector - Emitter Voltage	140V
V_{EBO}	Emitter - Base Voltage	10V
I_C	Continuous Collector Current	6A
I_B	Base Current	3A
P_{tot}	Total Power Dissipation at $T_{case} = 25^{\circ}\text{C}$ Derate above 25°C	50W 0.29 W/ $^{\circ}\text{C}$
T_J	Junction Temperature	200 $^{\circ}\text{C}$
T_{stg}	Storage Temperature	-65 to 200 $^{\circ}\text{C}$

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THERMAL CHARACTERISTICS

	Max	Unit
$R_{thj-case}$ Thermal resistance to case	3.5	°C/W

ELECTRICAL CHARACTERISTICS ($T_{case}=25^{\circ}C$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CEO} Collector Cut-Off Current	$V_{CE} = 140V$ $I_B = 0$			1.0	mA
I_{CES} Collector Cut-Off Current	$V_{CE} = 180V$ $V_{BE} = 0$			1.0	
I_{EBO} Emitter Cut-Off Current	$V_{EB} = 10V$ $I_C = 0$			1.0	
$V_{(BR)CEO}^*$ Collector-Emitter Breakdown Voltage	$I_C = 50mA$ $I_B = 0$	140			V
$V_{(BR)CBO}^*$ Collector-Base Breakdown Voltage	$I_C = 3mA$	200			
$V_{CE(sat)}^*$ Collector-Emitter Saturation Voltage	$I_C = 2.0A$ $I_B = 0.25A$			0.6	
$V_{BE(sat)}^*$ Base-Emitter Saturation Voltage	$I_C = 2.0A$ $I_B = 0.25A$			1.2	
h_{FE}^* Forward-current transfer ratio	$I_C = 1.0A$ $V_{CE} = 4.0V$		90		
	$I_C = 2.0A$ $V_{CE} = 4.0V$	75	82	100	

DYNAMIC CHARACTERISTICS

C_{obo} Output Capacitance	$I_E = 0$ $V_{CB} = 10V$ $f = 1.0MHz$		65	120	pF
F_T Transition Frequency	$I_C = 0.5A$ $V_{CE} = 15V$ $f = 10.0MHz$	10			MHz
T_{on} Turn-on time	$I_C = 5.0A$ $I_{B1} = 1.0A$		0.3	0.5	μs
T_{off} Turn-off time	$I_C = 5.0A$ $I_{B1} = -I_{B2} = 1.0A$		1.5	2.0	

* Pulse test $t_p = 300\mu s$, $\delta < 2\%$

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